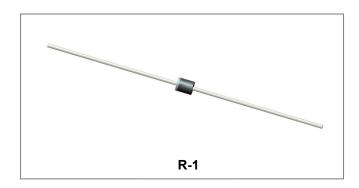






# 1A1 THRU 1A7 1.0A MINIATURE SILICON RECTIFIER



#### **Features**

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

# **Circuit Diagram**



#### **Mechanical Data**

• Case: R-1 Molded Plastic

• Terminals: Plated Leads Solderable Per MIL-

STD-202, Method 208
Polarity: Cathode Band

Weight: 0.181 grams(Approx)

#### Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Type Number	Symbol	1A1	1A2	1A3	1A4	1A5	1A6	1A7	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V <sub>RMS</sub>	35	70	140	280	420	560	700	V
Average forward rectified output current  @T <sub>A</sub> = 75°C	Io				1.0				Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	30				А			
Forward Voltage @I <sub>F</sub> =1.0A	V <sub>FM</sub>				1.0				V
Peak Reverse Current @T <sub>A</sub> = 25°C At Rated DC Blocking Voltage @T <sub>A</sub> = 100°C	I <sub>RM</sub>				5.0 50				μА
Typical Junction Capacitance (Note 2)	Сл				15				pF
Typical Thermal Resistance Junction to Ambient (Note 1)	R <sub>0JA</sub>	50			°C/W				
Operating Junction Temperature Range	TJ			-6	35 to +12	25			°C
Storage Temperature Range	T <sub>STG</sub>			-6	65 to +15	50			°C

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm form the case.

2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

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# **Ratings and Characteristics Curves**

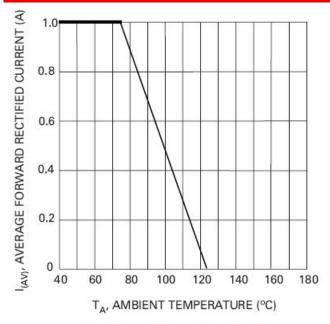


Fig. 1 Forward Current Derating Curve

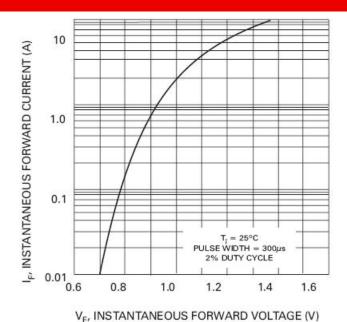


Fig. 2 Typical Forward Characteristics

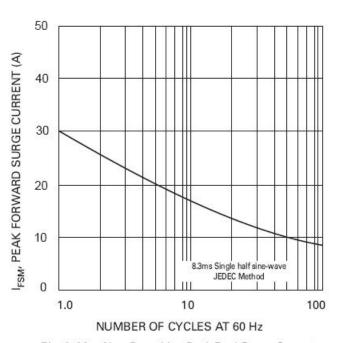


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

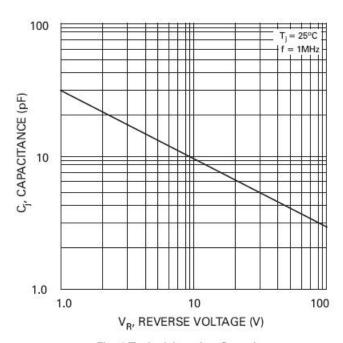


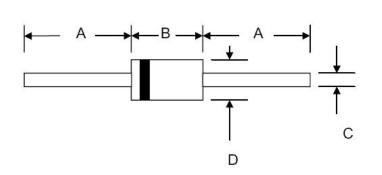
Fig. 4 Typical Junction Capacitance







## **Mechanical Dimensions R-1**



SYMBOL	Millim	neters	Inches			
OTIMBOL	Min.	Max.	Min.	Max.		
Α	20.0	-	0.787	-		
В	2.00	3.5	0.079	0.138		
С	0.53	0.64	0.021	0.025		
D	2.20	2.60	0.087	0.102		

## **Ordering Information**

Device	Package	Shipping
1A1-1A7	R-1 (Pb-Free)	5000pcs / tape

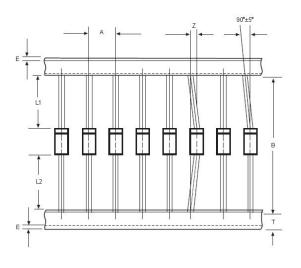
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Marking Diagram**



1A1 = Type Number

# **Carrier Tape Specification R-1**



SYMBOL	Millimeters			
	Min.	Max.		
А	9.5	10.5		
В	50.9	53.9		
Z	-	1.20		
Т	5.60	6.40		
E	-	0.80		
IL1-L2I	-	1.0		

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